

Amendments to the Specification

Please replace paragraph [0075] on page 20 with the following amended version of that paragraph:

Various deposition techniques may be employed to form the CDO dielectric materials of this invention. These include various other forms of chemical vapor deposition (CVD) including plasma enhanced CVD (PECVD) and high-density plasma CVD (HDP CVD). HDP CVD of dielectric materials is described in various sources including commonly assigned US Patent Application No. 09/996,619, filed November 28, 2001 by Atiye Bayman et al. and titled "Gap Fill for High Aspect Ratio Structures" (now US Patent No. 6,596,654), which is incorporated herein by reference for all purposes. Additionally, other techniques such as spin on techniques and deposition from supercritical solutions may be employed. But for many applications of this invention, a plasma based CVD process is employed.